

Title (en)
High-density plasma source for ionized metal deposition

Title (de)
Plasmaquelle hoher Dichte für ionisierter Metall Metallabscheidung

Title (fr)
Source de plasma à haute densité pour dépôt métallique ionisé

Publication
EP 1076352 A3 20051123 (EN)

Application
EP 00306909 A 20000814

Priority
US 37309799 A 19990812

Abstract (en)
[origin: US6183614B1] A magnetron especially advantageous for low-pressure plasma sputtering or sustained self-sputtering having reduced area but full target coverage. The magnetron includes an outer pole face surrounding an inner pole face with a gap therebetween. The outer pole of the magnetron of the invention is smaller than that of a circular magnetron similarly extending from the center to the periphery of the target. Different shapes include a racetrack, an ellipse, an egg shape, a triangle, and a triangle with an arc conforming to the target periphery. The small shape allows high power densities to be applied to the area of the target actually being sputtered. Preferably, the magnetic flux produced by the outer pole is greater than that produced by the inner pole. The asymmetry provides several advantages in high-density plasma sputtering. The invention allows sustained self-sputtering of copper and allows sputtering of aluminum, titanium, and other metal at reduced pressures down to at least 0.1 milliTor. However, at least for titanium, bottom coverage is improved for higher chamber pressures. For some metals, the pedestal bearing the wafer should be RF biased to a limited degree. The invention allows ionization fractions of the metal of 20% and greater with only the use of capacitive power coupling and can produce bottom coverage of greater than 25% in a hole having an aspect ratio of 5.

IPC 1-7
H01J 37/34

IPC 8 full level
C23C 14/35 (2006.01); **H01J 37/34** (2006.01); **H01L 21/203** (2006.01); **H01L 21/28** (2006.01); **H01L 21/285** (2006.01); **H05H 1/46** (2006.01)

CPC (source: EP KR US)
C23C 14/35 (2013.01 - KR); **H01J 37/3408** (2013.01 - EP KR US); **H01J 37/3455** (2013.01 - EP KR US)

Citation (search report)

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Designated contracting state (EPC)
AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE

DOCDB simple family (publication)
US 6183614 B1 20010206; EP 1076352 A2 20010214; EP 1076352 A3 20051123; JP 2001140070 A 20010522; JP 4936584 B2 20120523; KR 100806988 B1 20080225; KR 20010021283 A 20010315; SG 87153 A1 20020319; TW 486718 B 20020511

DOCDB simple family (application)
US 37309799 A 19990812; EP 00306909 A 20000814; JP 2000246012 A 20000814; KR 20000046753 A 20000812; SG 200004437 A 20000811; TW 89116293 A 20000811